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2N3905



PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 100 mA.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

| Symbol | Parameter | Value | Units |
|-----------------------------------|--|-------------|-------|
| V_{CEO} | Collector-Emitter Voltage | 40 | V |
| V _{CBO} | Collector-Base Voltage | 40 | V |
| V _{EBO} | Emitter-Base Voltage | 5.0 | V |
| Ic | Collector Current - Continuous | 200 | mA |
| T _J , T _{stg} | Operating and Storage Junction Temperature Range | -55 to +150 | °C |

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics TA = 25°C unless otherwise noted

| Symbol | Characteristic | Мах | Units |
|------------------|---|------------|-------------|
| | | 2N3905 | |
| P _D | Total Device Dissipation Derate above 25°C | 625 5.0 | mW mW/°C |
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 83.3 | °C/W |
| R _{0JA} | Thermal Resistance, Junction to Ambient | 200 | °C/W |

PNP General Purpose Amplifier (continued)

| OFF CHAI | Falailletei | Test Conditions | Min | Max | Units |
|----------------------|---|--|----------|-----------------|-------------------|
| | | | | | |
| V(BR)CEO | RACTERISTICS | 10 - 0 | 40 | | V |
| M | Collector-Emilier Breakdown Voltage | $I_{\rm C} = 1.0$ IIIA, $I_{\rm B} = 0$ | 40 | | V |
| V _{(BR)CBO} | Emitter Rase Breakdown Voltage | $I_{\rm C} = 10 \mu{\rm A}, I_{\rm E} = 0$ | 40 | | V |
| V (BR)EBO | Collector Cutoff Current | $I_{\rm E} = 10 \mu {\rm A}, I_{\rm C} = 0$ | 5.0 | 50 | v nA |
| | Base Cutoff Current | $V_{CE} = 30 V, V_{OB} = 3.0 V$ | | 50 | nA nA |
| BL | Dase Outon Current | $v_{CE} = 30 v, v_{OB} = 3.0 v$ | | 50 | IIA |
| ON CHAR | ACTERISTICS* | | | | |
| η _{FE} | DC Current Gain | $V_{CE} = 1.0 \text{ V}, I_{C} = 0.1 \text{ mA}$ | 30 | | |
| | | $V_{CE} = 1.0 \text{ V}, I_{C} = 1.0 \text{ mA}$ | 40 | 4.50 | |
| | | $V_{CE} = 1.0 \text{ V}, I_C = 10 \text{ mA}$ $V_{CE} = 1.0 \text{ V}, I_C = 50 \text{ mA}$ | 50 30 | 150 | |
| | | $V_{CE} = 1.0 \text{ V}, I_C = 100 \text{ mA}$ | 15 | | |
| V _{CE(sat)} | Collector-Emitter Saturation Voltage | $I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 1.0 \text{ mA}$ | | 0.25 | V |
| V | Base-Emitter Saturation Voltage | $I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$ | 0.65 | 0.40 | V |
| VBE(sat) | Base Emilier Galdralion Voltage | $I_{\rm C} = 50 \text{ mA}, I_{\rm B} = 5.0 \text{ mA}$ | 0.00 | 0.95 | v |
| C _{ib} | Input Capacitance | $V_{EB} = 0.5 V, f = 1.0 MHz$ | 0.0 | 10 | pF |
| C _{ib} | Input Capacitance | $V_{EB} = 0.5 V, f = 1.0 MHz$ | | 10 | pF |
| lfe | Smail-Signal Current Gain | $f_{C} = 10 \text{ mA}, v_{CE} = 20 \text{ v},$ f = 100 MHz | 2.0 | | |
| hfe | Small-Signal Current Gain | $I_{\rm C} = 1.0 {\rm mA}, V_{\rm CE} = 10 {\rm V},$ | 50 | 200 | |
| า _{re} | Voltage Feedback Ratio | f = 1.0 KHz | 0.1 | 5.0 | x10 ⁻⁴ |
| Nie | Input Impedance | | 0.5 | 8.0 | kΩ |
| loe | Output Impedance | | 1.0 | 40 | μmhos |
| | Noise Figure | $V_{CE} = 5.0$ V, $I_C = 100$ μA, $R_S = 1.0$ kΩ, $R_W = 10$ Hz to 15.7 KHz | | 5.0 | dB |
| NF | 1 | | | | |
| SWITCHIN | NG CHABACTERISTICS | | | | |
| SWITCHIN | NG CHARACTERISTICS Delay Time | $V_{cc} = 3.0 \text{ V}, I_{cs} = 10 \text{ mA},$ | | 35 | ns |
| | NG CHARACTERISTICS Delay Time Rise Time | $V_{cc} = 3.0 \text{ V}, I_{cs} = 10 \text{ mA},$ $I_{B1} = 1.0 \text{ mA}, V_{OB (off)} = 3.0 \text{ V}$ | | 35 35 | ns ns |
| SWITCHIN | NG CHARACTERISTICS Delay Time Rise Time Storage Time | $V_{\rm CC} = 3.0 \text{ V}, I_{\rm CS} = 10 \text{ mA},$ $I_{\rm B1} = 1.0 \text{ mA}, V_{\rm OB \ (off \)} = 3.0 \text{ V}$ $V_{\rm CC} = 3.0 \text{ V}, I_{\rm CS} = 10 \text{ mA},$ | | 35 35 200 | ns ns ns |

2N3905

2N3905

PNP General Purpose Amplifier (continued)





PNP General Purpose Amplifier (continued) Typical Characteristics (continued) **Noise Figure vs Frequency Noise Figure vs Source Resistance** 6 12 V_{CE} = 5.0V V_{CE} = 5.0V f = 1.0 kHz**10** 8 6 4 - NOISE FIGURE (dB) : 1.0 m C: I C = 100 μ A, R S = 200 Ω $C = 1.0 \text{ mA}, R_S = 200\Omega$ I_C = 100 μA ≝ 1 ۳ 2 _I_C = 100 μA, R_S = 2.0 kΩ_ ĬШЕ 0 L 0 L 0.1 10 100 1 10 100 f - FREQUENCY (kHz) R _S - SOURCE RESISTANCE ($k\Omega$) **Switching Times** Turn On and Turn Off Times vs Collector Current vs Collector Current 500 500 t off 100 100 TIME (nS) TIME (nS) $t_{on} I_{B1} = \frac{10}{10}$ ⁱ on $V_{BE(OFF)} = 0.5V$ 10 10 t_{off} I_{B1}= I_{B2}= 10 I_{B1}= I_{B2}= 10 Г 1 1 10 I c - COLLECTOR CURRENT (mA) 100 1 100 10 I - COLLECTOR CURRENT (mA) **Power Dissipation vs Ambient Temperature P** - **DOWER DISSIPATION (W)** 0.50 0.25 SOT-223 TO-92 SOT-23 0 L 25 50 75 100 TEMPERATURE (°C) 125 150



²N3905

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|--------------------------|---------------------------|---|
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